Sergey Pushkarev

List of Publications by Year
in descending order

44	231	1162367 8	1199166 12
papers	citations	h-index	g-index

45	45	45	169
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	X-ray Diffraction Analysis of the Structure In0.53Ga0.47As Films Grown on (100) and (111)A GaAs Substrates with a Metamorphic Buffer. Crystallography Reports, 2022, 67, 317-322.	0.1	2
2	Study of the Surface Morphology, Electrophysical Characteristics, and Photoluminescence Spectra of GaAs Epitaxial Films on GaAs(110) Substrates. Optics and Spectroscopy (English Translation of) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50	0.2	1
3	Silicon-Doped Epitaxial Films Grown on GaAs(110) Substrates: the Surface Morphology, Electrical Characteristics, and Photoluminescence Spectra. Semiconductors, 2020, 54, 1417-1423.	0.2	1
4	Structural Characteristics of Epitaxial Low-Temperature Grown {InGaAs/InAlAs} Superlattices on InP(100) and InP(111)A Substrates. Crystallography Reports, 2020, 65, 496-501.	0.1	2
5	Improved InGaAs and InGaAs/InAlAs Photoconductive Antennas Based on (111)-Oriented Substrates. Electronics (Switzerland), 2020, 9, 495.	1.8	10
6	New Structure for Photoconductive Antennas Based on {LTG-GaAs/GaAs:Si} Superlattice on GaAs(111)A Substrate. Crystallography Reports, 2019, 64, 205-211.	0.1	7
7	Electrical and Photoluminescence Studies of {LT-GaAs/GaAs:Si} Superlattices Grown by MBE on (100)- and (111)A-Oriented GaAs Substrates. Semiconductors, 2019, 53, 246-254.	0.2	2
8	Enhanced terahertz emission from strain-induced InGaAs/InAlAs superlattices. Journal of Applied Physics, 2019, 125, .	1.1	31
9	Photoluminescence Studies of Si-Doped Epitaxial GaAs Films Grown on (100)- and (111)A-Oriented GaAs Substrates at Lowered Temperatures. Semiconductors, 2018, 52, 376-382.	0.2	6
10	Photoconductive antennas based on epitaxial films In0.5Ga0.5As on GaAs (1â€‰1â€‰1)A and (1â€‰0â€‰0)A substrates with a metamorphic buffer. Laser Physics Letters, 2018, 15, 076201.	0.6	7
11	X-Ray Diffraction Analysis of Features of the Crystal Structure of GaN/Al0.32Ga0.68N HEMT-Heterostructures by the Williamsonâ€“Hall Method. Semiconductors, 2018, 52, 734-738.	0.2	3
12	Photoconductive antennas based on epitaxial films In0.5Ga0.5As on GaAs (1â€‰1â€‰1)A and (1â€‰0â€‰0) substrates with a metamorphic buffer. Laser Physics, 2018, 28, 076206.	0.6	0
13	Influence of arsenic flow on the crystal structure of epitaxial GaAs grown at low temperatures on GaAs (100) and (111)A substrates. Crystallography Reports, 2017, 62, 82-90.	0.1	5
14	Terahertz-radiation generation and detection in low-temperature-grown GaAs epitaxial films on GaAs (100) and (111)A substrates. Semiconductors, 2017, 51, 503-508.	0.2	15
15	X-ray analysis of multilayer In0.52Al0.48As/In0.53Ga0.47As/In0.52Al0.48As HEMT heterostructures with InAs nanoinsert in quantum well. Crystallography Reports, 2017, 62, 355-363.	0.1	5
16	Ultrafast carrier dynamics in LT-GaAs doped with Si delta layers. International Journal of Modern Physics B, 2017, 31, 1750195.	1.0	6
17	Terahertz-radiation generation in low-temperature InGaAs epitaxial films on (100) and (411) InP substrates. Semiconductors, 2017, 51, 310-317.	0.2	13
18	Epitaxial low-temperature growth of In0.5Ga0.5As films on GaAs(100) and GaAs(111)A substrates using a metamorphic buffer. Crystallography Reports, 2017, 62, 947-954.	0.1	1

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19	Low-Temperature epitaxial growth of InGaAs films on InP(100) and InP(411)A substrates. Crystallography Reports, 2017, 62, 589-596.	0.1	0
20	Electron properties of surface InGaAs/InAlAs quantum wells with inverted doping on InP substrates. Semiconductors, 2017, 51, 760-765.	0.2	0
21	Features of the diagnostics of metamorphic InAlAs/InGaAs/InAlAs nanoheterostructures by high-resolution X-ray diffraction in the ï‰-scanning mode. Semiconductors, 2016, 50, 559-565.	0.2	9
22	Structural and photoluminescence properties of low-temperature GaAs grown on GaAs(100) and GaAs(111)A substrates. Semiconductors, 2016, 50, 195-203.	0.2	8
23	Generation of THz radiation in epitaxial InGaAs films on InP substates of various crystallographic orientations. , 2016, , .		0
24	High-resolution X-ray diffractometry and transmission electron microscopy as applied to the structural study of InAlAs/InGaAs/InAlAs multilayer transistor nanoheterostructures. Journal of Surface Investigation, 2016, 10, 495-509.	0.1	1
25	Influence of buffer-layer construction and substrate orientation on the electron mobilities in metamorphic In0.70Al0.30As/In0.76Ga0.24As/In0.70Al0.30As structures on GaAs substrates. Semiconductors, 2015, 49, 921-929.	0.2	6
26	Structural and electrophysical properties of In0.52Al0.48As/In0.53Ga0.47As/In0.52Al0.48As/InP HEMT nanoheterostructures with different combinations of InAs and GaAs inserts in quantum well. Crystallography Reports, 2015, 60, 397-405.	0.1	1
27	Specific features of the photoluminescence of HEMT nanoheterostructures containing a composite InAlAs/InGaAs/InAs/InGaAs/InAlAs quantum well. Semiconductors, 2015, 49, 234-241.	0.2	12
28	Photoluminescence properties of modulation-doped In x Al1â€“x As/In y Ga1â€“y As/In x Al1â€“x As structures with strained inas and gaas nanoinserts in the quantum well. Semiconductors, 2015, 49, 1207-1217.	0.2	5
29	Electrophysical and structural properties of the composite quantum wells In_{0.52}Al_{0.48}As/In_xGa_{1â^'x}As/In_{0.52}Al_{0.48}As with ultrathin InAs inserts. Journal of Materials Research, 2015, 30, 3020-3025.	0.1	5
30	Structural and electrical properties of InAlAs/InGaAs/InAlAs HEMT heterostructures on InP substrates with InAs inserts in quantum well. Crystallography Reports, 2014, 59, 900-907.	0.1	3
31	Effect of GaAs (100) substrate misorientation on the electrical parameters and surface morphology of metamorphic In0.7Al0.3As/In0.75Ga0.25As/In0.7Al0.3As HEMT nanoheterostructures. Semiconductors, 2014, 48, 63-68.	0.2	1
32	Application of photoluminescence spectroscopy to studies of In0.38Al0.62As/In0.38Ga0.62As/GaAs metamorphic nanoheterostructures. Semiconductors, 2014, 48, 883-890.	0.2	4
33	X-Ray diffractometry of metamorphic nanoheterostructures. Crystallography Reports, 2014, 59, 258-265.	0.1	8
34	Electrophysical characteristics and structural parameters of metamorphic HEMT nanoheterostructures In0.7Al0.3As/In0.7Ga0.3As/In0.7Al0.3As containing superlattices with different numbers of periods in the metamorphic buffer. Crystallography Reports, 2014, 59, 425-429.	0.1	2
35	Photoluminescence studies of In0.7Al0.3As/In0.75Ga0.25As/In0.7Al0.3As metamorphic heterostructures on GaAs substrates. Semiconductors, 2014, 48, 640-648.	0.2	8
36	Investigation of In0.7Ga0.3As/In0.7Al0.3As metamorphic HEMT- heterostructures by photoluminescence spectroscopy. Journal of Physics: Conference Series, 2014, 541, 012080.	0.3	4

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37	Study of new designs for the InAlAs metamorphic buffer on GaAs substrates with distributed compensation of elastic deformations. Semiconductors, 2013, 47, 997-1002.	0.2	8
38	Study of the influence of strained superlattices introduced into a metamorphic buffer on the electrophysical properties and the atomic structure of InAlAs/InGaAs MHEMT heterostructures. Semiconductors, 2013, 47, 532-537.	0.2	4
39	Electrical and structural characteristics of metamorphic In0.38Al0.62As/In0.37Ga0.63As/In0.38Al0.62As HEMT nanoheterostructures. Crystallography Reports, 2013, 58, 914-919.	0.1	2
40	Maximum drift velocity of electrons in selectively doped InAlAs/InGaAs/InAlAs heterostructures with InAs inserts. Semiconductors, 2013, 47, 372-375.	0.2	9
41	Influence of metamorphic buffer design on electrophysical and structural properties of MHEMT nanoheterostructures In_{0.7}Al_{0.3}As/In_{0.7}Ga_{0.3}As/In_{0.7}Al_{0.3}As/GaAs. Proceedings of SPIE, 2013, . .	0.8	0
42	Structural and electrophysical analysis of MHEMT In0.70Al0.30As/In0.75Ga0.25As nanoheterostructures with different strain distributions in metamorphic buffer. Crystallography Reports, 2012, 57, 841-847.	0.1	2
43	Structural and electrical properties of metamorphic nanoheterostructures with a high InAs content (37â€“100%) grown on GaAs and InP substrates. Crystallography Reports, 2011, 56, 875-879.	0.1	2
44	Interrelation of the construction of the metamorphic InAlAs/InGaAs nanoheterostructures with the InAs content in the active layer of 76â€“100% with their surface morphology and electrical properties. Semiconductors, 2011, 45, 1158-1163.	0.2	9